

1MBI1000VXB-170EH-54

IGBT Modules

IGBT MODULE (V series) 1700V / 1000A / 1 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- NPC 3-level Inverter
- Active PFC
- Industrial machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Collector-Emitter voltage	V_{CES}		1700	V	
Gate-Emitter voltage	V_{GES}		± 20	V	
Collector current	I_c	Continuous	$T_c=25^\circ\text{C}$ 1400	A	
	I_c pluse	1ms	$T_c=100^\circ\text{C}$ 1000		
	$-I_c$		2000		
	$-I_c$ pluse	1ms	1000		
Collector Power Dissipation	P_c	1 device	6250	W	
Reverse voltage for FWD	V_R		1700	V	
Forword current for FWD	I_F	Continuous	1000	A	
	I_F pulse	1ms	2000		
Junction temperature	T_j		175	$^\circ\text{C}$	
Operating junction temperature (under switching conditions)	T_{jop}		150		
Case temperature	T_c		150		
Storage temperature	T_{stg}		-40 ~ +150		
Isolation voltage	between terminal and copper base (*1)	V_{iso}	AC : 1min.	4000	VAC
	between thermistor and others (*2)				
Screw Torque (*3)	Mounting	-	M5	6.0	N m
	Main Terminals	-	M8	10.0	
	Sense Terminals	-	M4	2.1	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value : Mounting 3.0 ~ 6.0 Nm (M5)
 Recommendable Value : Main Terminals 8.0 ~ 10.0 Nm (M8)
 Recommendable Value : Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at T_J= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
IGBT+Inverse Diode	Zero gate voltage collector current	I _{CEs}	V _{CE} = 1700V V _{GE} = 0V	-	-	6.0	mA	
	Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V V _{GE} = ±20V	-	-	1200	nA	
	Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V I _c = 1000mA	6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V _{CE(sat)} (terminal) (*4)	I _c = 1000A V _{GE} = 15V	T _J = 25°C	-	2.10	2.55	V
				T _J = 125°C	-	2.50	-	
				T _J = 150°C	-	2.55	-	
		T _J = 25°C		-	2.00	2.45		
		T _J = 125°C		-	2.40	-		
	V _{CE(sat)} (chip)	T _J = 150°C	-	2.45	-			
	Internal gate resistance	R _{G(int)}	-	-	1.17	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	94	-	nF		
Turn-on time	t _{on}	V _{CC} = 900V I _c = 1000A	-	1250	-	nsec		
	t _r	V _{GE} = ±15V	-	500	-			
	t _{r(t)}	R _G = +1.2 / -1.8 Ω	-	150	-			
	t _{off}	L _S = 60nH	-	1550	-			
Turn-off time	t _r	-	-	150	-	nsec		
	t _r	-	-	150	-			
Forward on voltage	V _F (terminal) (*4)	I _F = 1000A V _{GE} = 0V	T _J = 25°C	-	1.95	2.40	V	
			T _J = 125°C	-	2.20	-		
			T _J = 150°C	-	2.15	-		
	T _J = 25°C		-	1.85	2.30			
	T _J = 125°C		-	2.10	-			
V _F (chip)	T _J = 150°C	-	2.05	-				
Reverse recovery time	t _{rr}	I _F = 1000A	-	240	-	nsec		
Reverse Current	I _R	V _{CE} = 1700V	-	-	3.0	mA		
FWD	V _F (terminal) (*4)	I _F = 1000A V _{GE} = 0V	T _J = 25°C	-	1.95	2.40	V	
			T _J = 125°C	-	2.20	-		
			T _J = 150°C	-	2.15	-		
	T _J = 25°C		-	1.85	2.30			
	T _J = 125°C		-	2.10	-			
V _F (chip)	T _J = 150°C	-	2.05	-				
Reverse recovery time	t _{rr}	I _F = 1000A	-	240	-	nsec		
Thermistor	Resistance	R	T = 25°C	-	5000	-	Ω	
		R	T = 100°C	465	495	520		
B value	B	T = 25/50°C	3305	3375	3450	K		

Note *4: Fuji defined V_{CE} value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

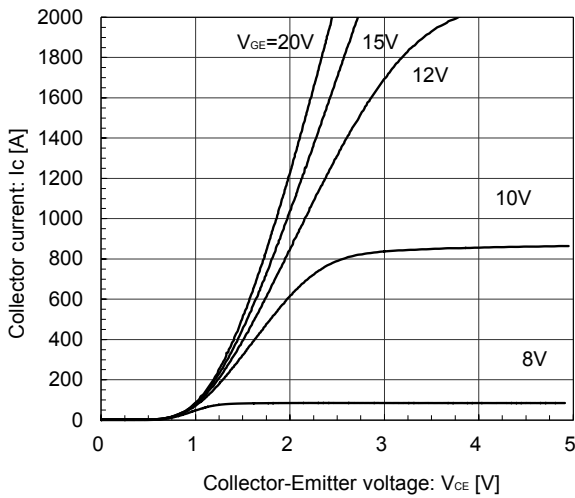
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance(1device)	R _{th(j-c)}	Inverter IGBT	-	-	0.024	°C/W
		Inverse Diode	-	-	0.048	
		FWD	-	-	0.048	
Contact thermal resistance (1device) (*5)	R _{th(c-f)}	with Thermal Compound	-	0.0083	-	

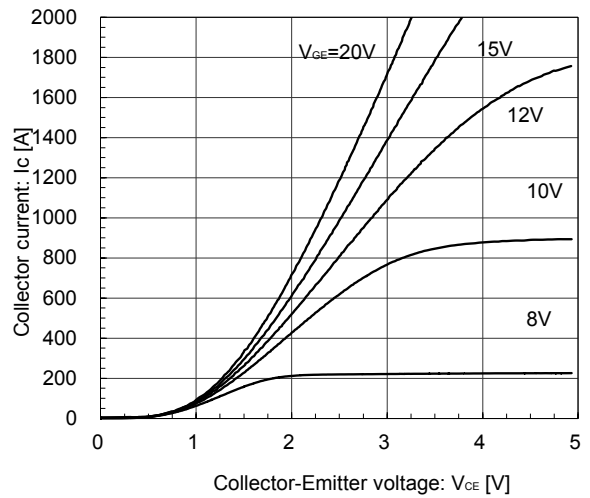
Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

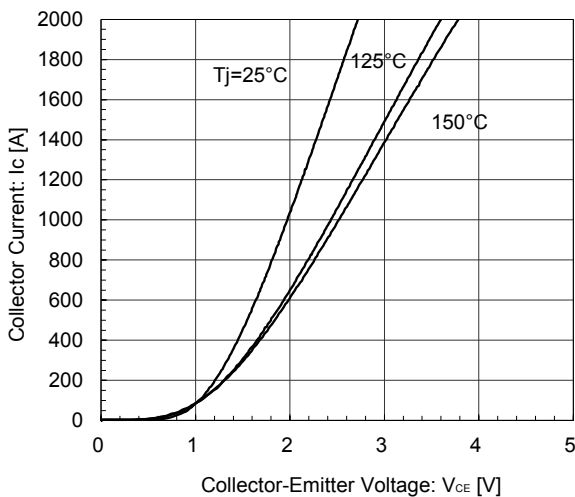
Collector current vs. Collector-Emittor voltage (typ.)
T_j= 25°C / chip



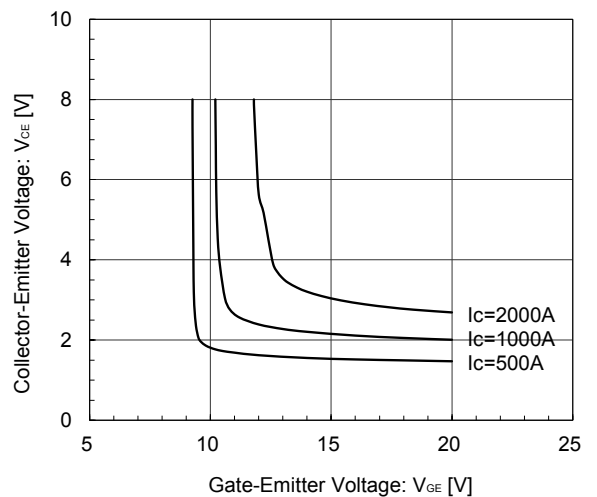
Collector current vs. Collector-Emittor voltage (typ.)
T_j= 150°C / chip



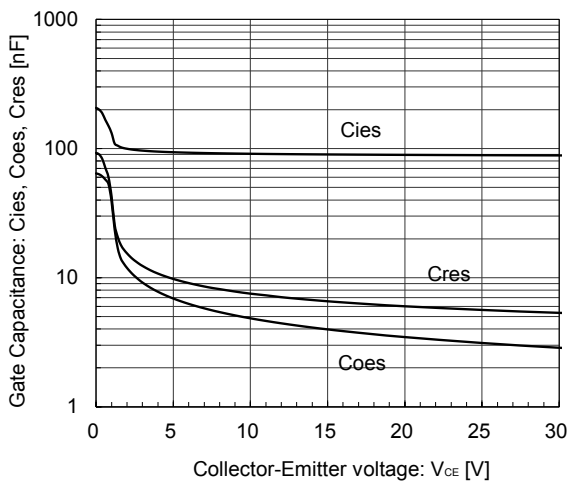
Collector current vs. Collector-Emittor voltage (typ.)
V_{ge}= 15V / chip



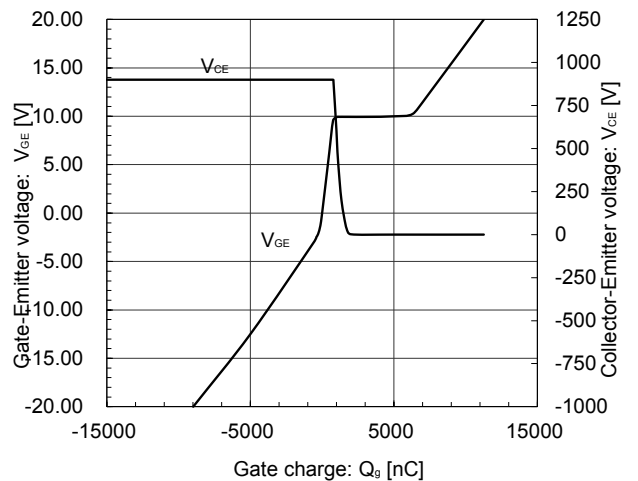
Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)
T_j= 25°C / chip



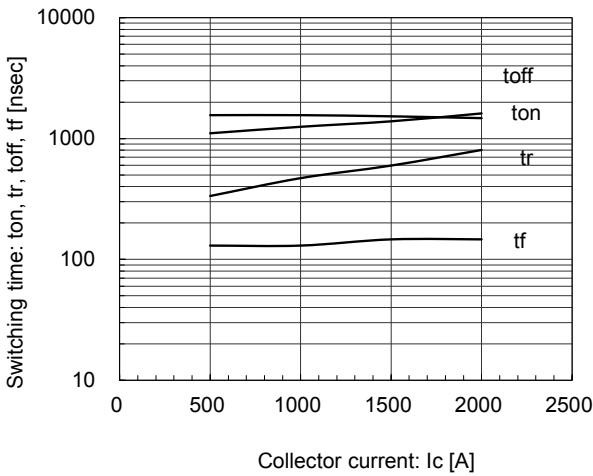
Gate Capacitance vs. Collector-Emittor Voltage (typ.)
V_{ge}= 0V, f= 1MHz, T_j= 25°C



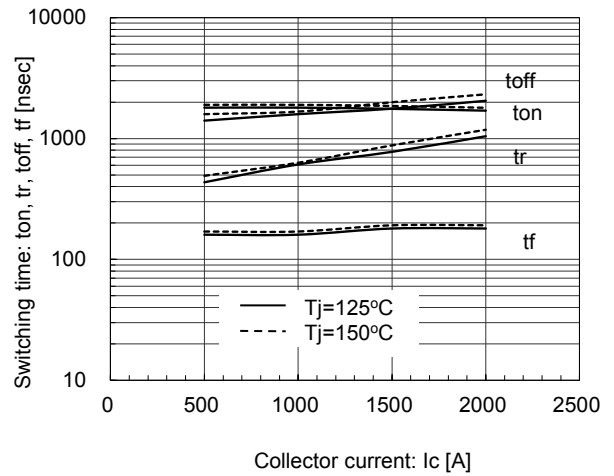
Dynamic Gate Charge (typ.)
V_{cc}=900V, Ic=1000A, T_j= 25°C



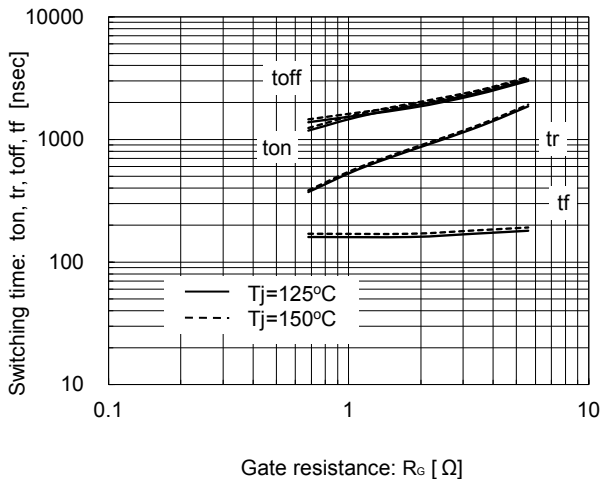
Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=+1.2/-1.8\Omega, T_j=25^\circ C$



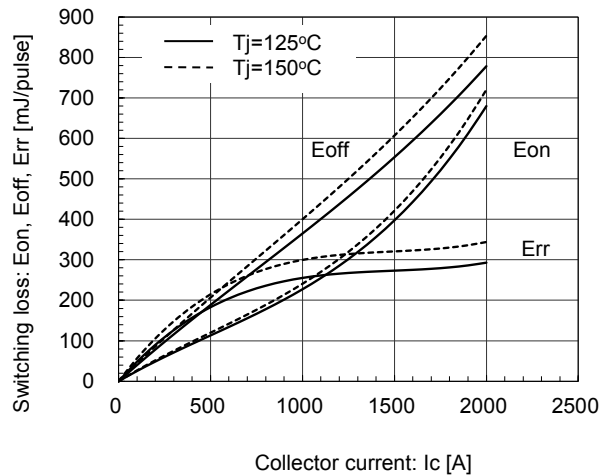
Switching time vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=+1.2/-1.8\Omega, T_j=125^\circ C, 150^\circ C$



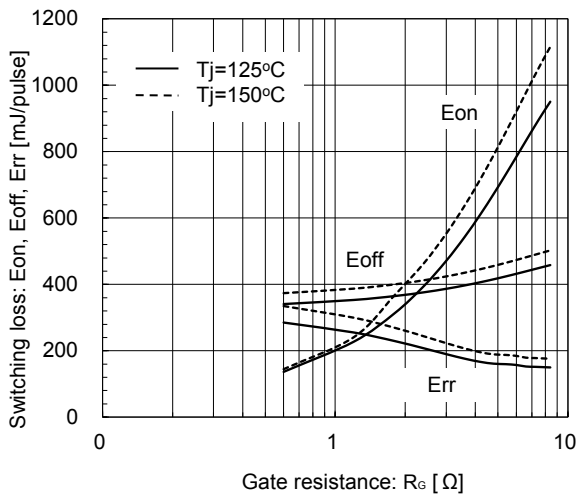
Switching time vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=1000A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



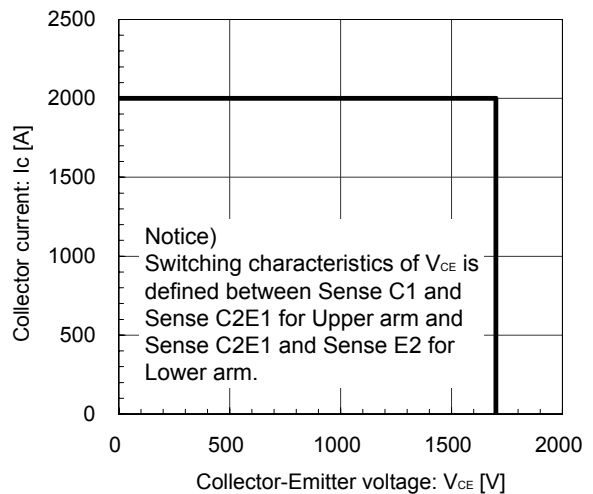
Switching loss vs. Collector current (typ.)
 $V_{CC}=900V, V_{GE}=\pm 15V, R_G=+1.2/-1.8\Omega, T_j=125^\circ C, 150^\circ C$

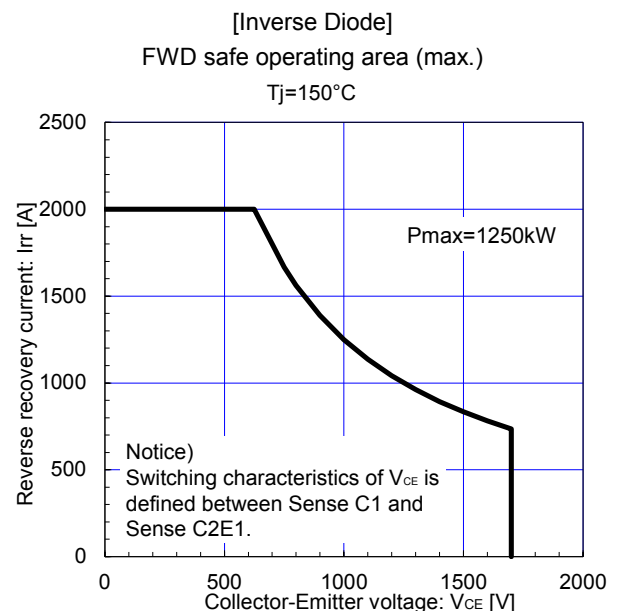
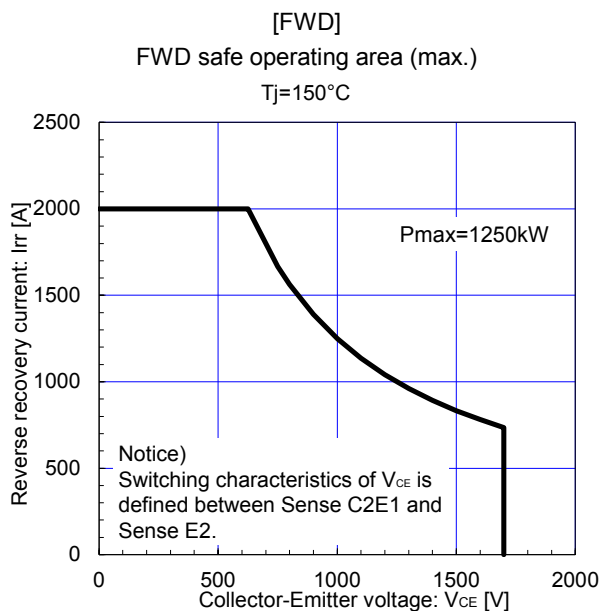
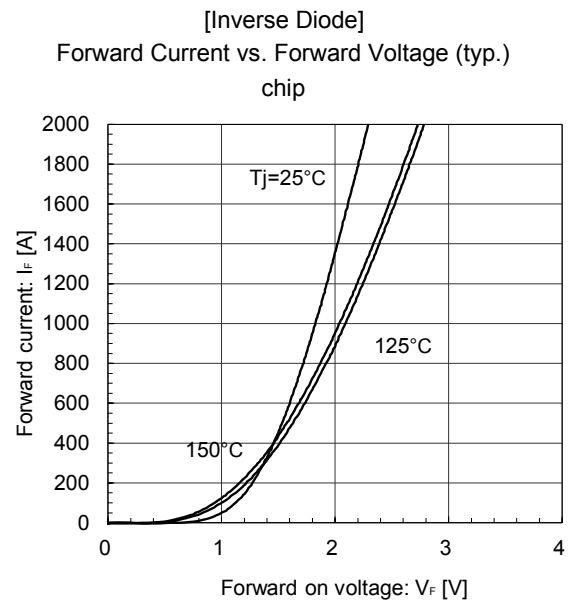
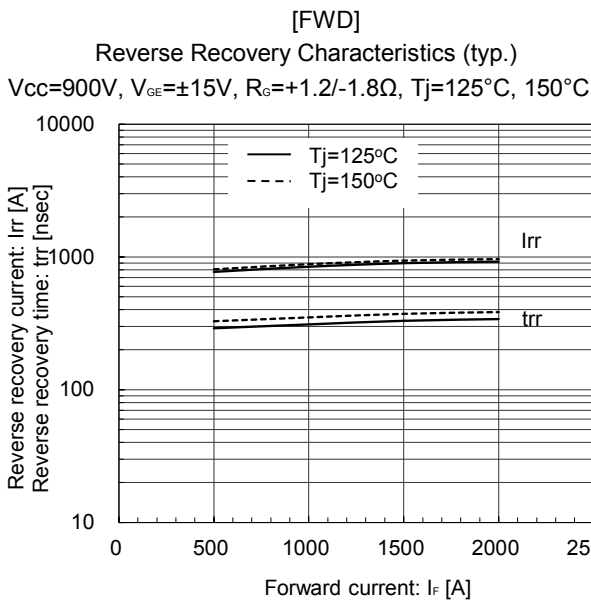
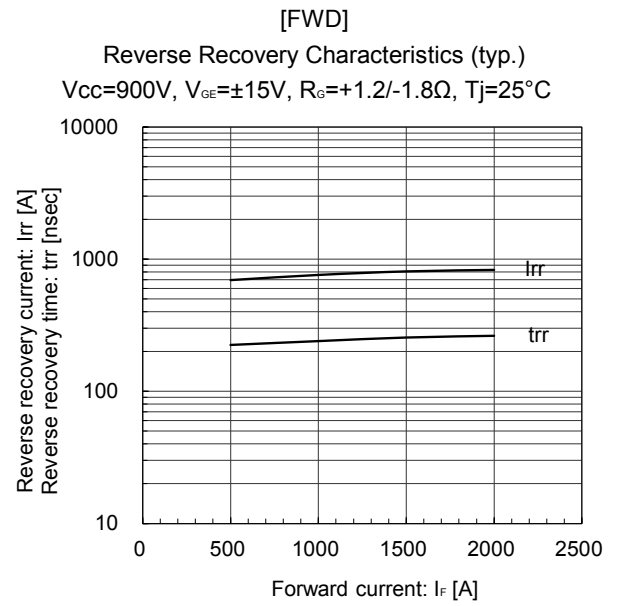
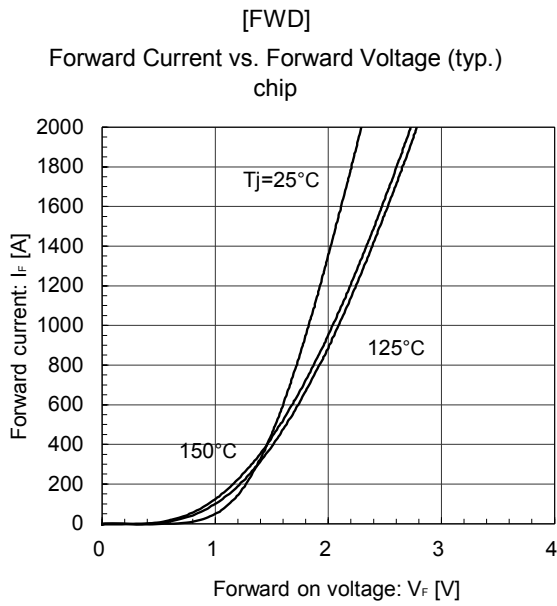


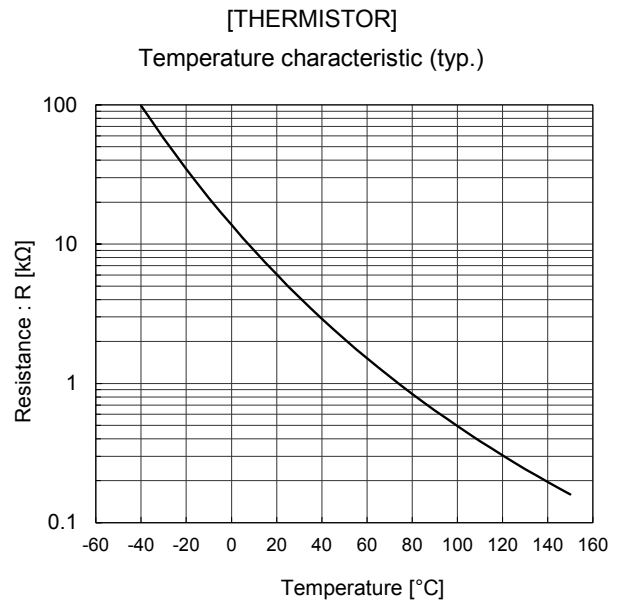
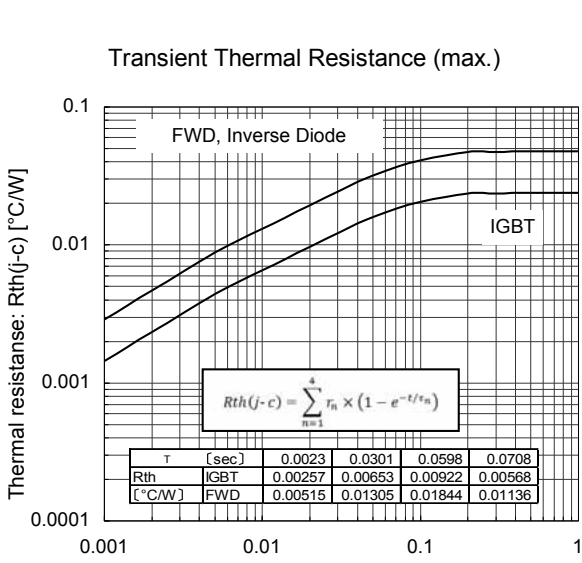
Switching loss vs. Gate resistance (typ.)
 $V_{CC}=900V, I_c=1000A, V_{GE}=\pm 15V, T_j=125^\circ C, 150^\circ C$



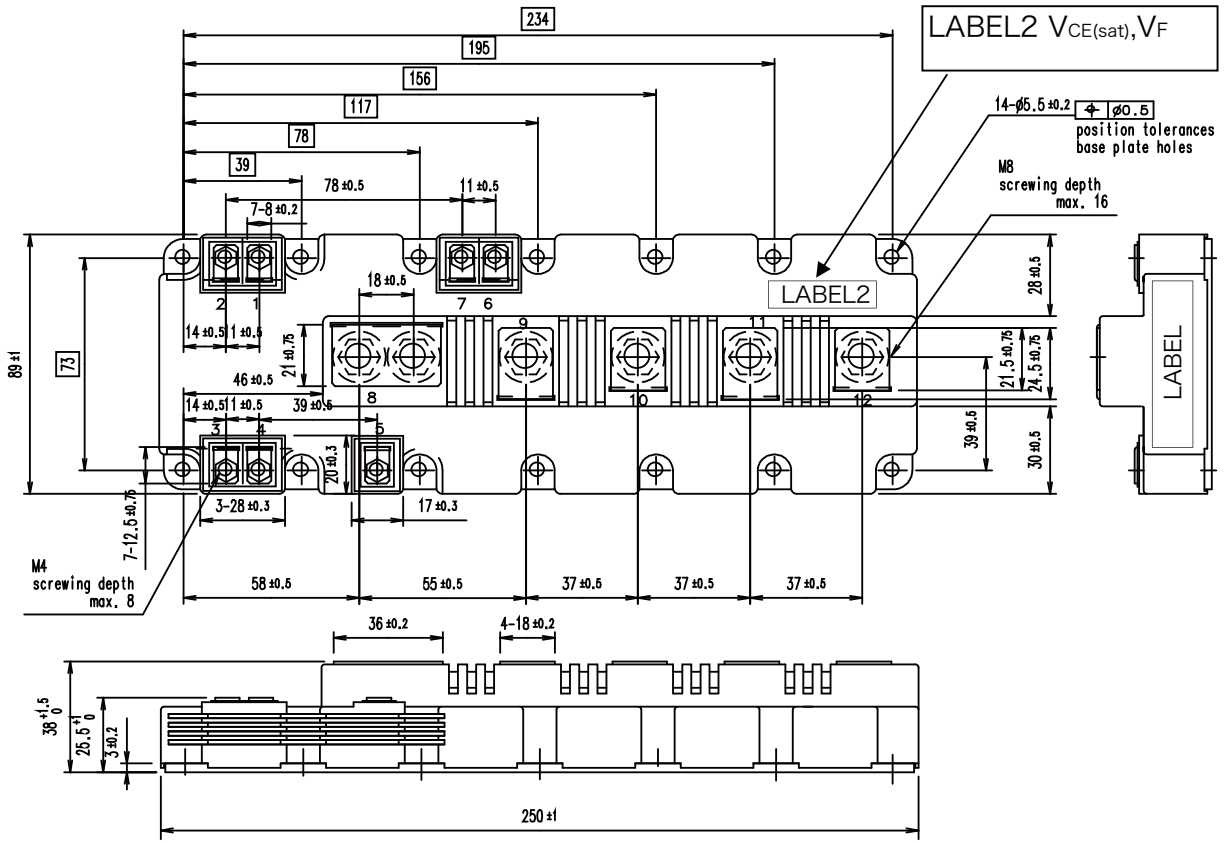
Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=\pm 15V, R_G=+1.2/-1.8\Omega, T_j=150^\circ C$





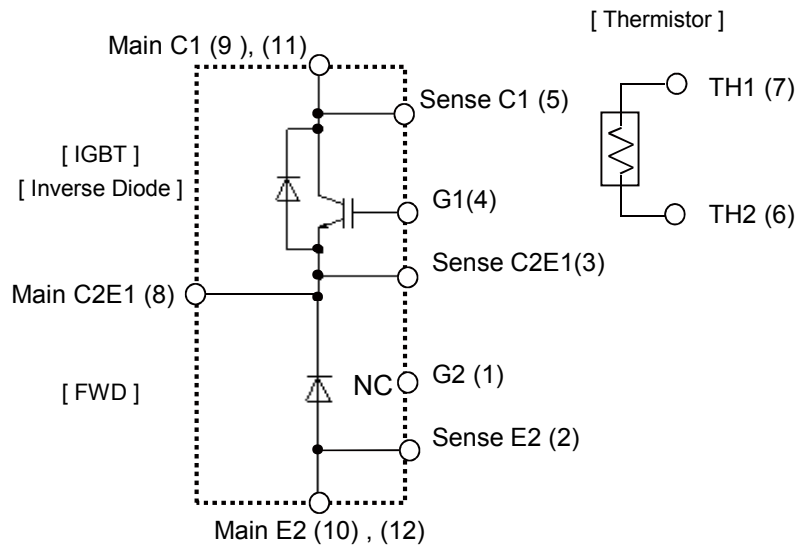


■ Outline Drawings, mm



Weight: 1250g(typ.)

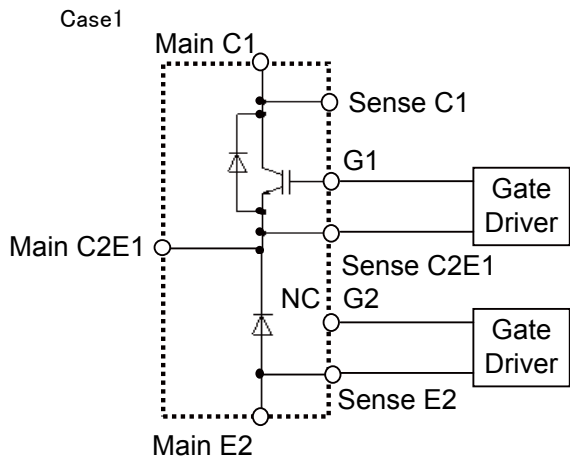
Equivalent Circuit Schematic



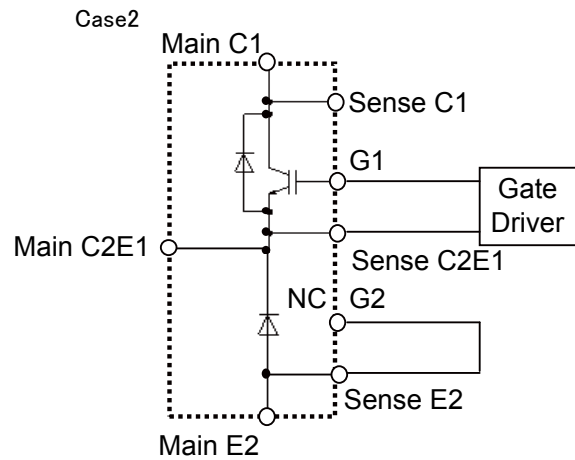
NOTICE

There is recommendation of wiring for NC terminal as follows.

Fuji recommends wire connection of CASE1 or CASE2 to fix NC terminal voltage.



NC terminal (G2) and sense E2 should be connected by Gate-Driver.



NC terminal (G2) and sense E2 should be connected by wire.

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IGBT Modules

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